

MOSFET – Dual, N-Channel, Asymmetric, Power Clip, POWER trench[®], 30 V

FDPC8013S

General Description

This device includes two specialized N-Channel MOSFETs in a dual package. The switch node has been internally connected to enable easy placement and routing of synchronous buck converters. The control MOSFET (Q1) and synchronous SyncFET™ (Q2) have been designed to provide optimal power efficiency.

Features

Q1: N-Channel

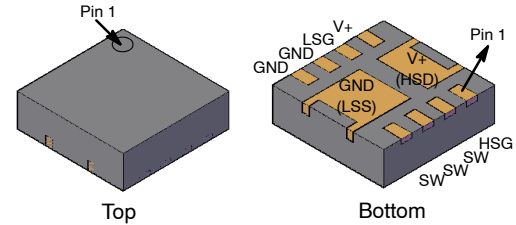
- Max $R_{DS(on)}$ = 9.6 mΩ at V_{GS} = 4.5 V, I_D = 10 A

Q2: N-Channel

- Max $R_{DS(on)}$ = 2.7 mΩ at V_{GS} = 4.5 V, I_D = 22 A
- Low Inductance Packaging Shortens Rise/Fall Times, Resulting in Lower Switching Losses
- MOSFET Integration Enables Optimum Layout for Lower Circuit Inductance and Reduced Switch Node Ringing
- RoHS Compliant

Applications

- Computing
- Communications
- General Purpose Point of Load



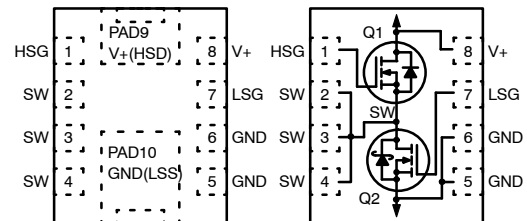
PQFN8 3.3 × 3.3, 0.65P
CASE 483AZ

MARKING DIAGRAM

&Z&3&K
13CF
15CF

&Z = Assembly Plant Code
 &3 = 3-Digit Date Code
 &K = 2-Digits Lot Run Traceability Code
 13CF15CF = Device Code

PIN ASSIGNMENT



ORDERING INFORMATION

Device	Package	Shipping†
FDPC8013S	PQFN8	3000 / Tape & Reel

†For information on tape and reel specifications, including part orientation and tape sizes, please refer to our Tape and Reel Packaging Specification Brochure, BRD8011/D.

FDPC8013S

MOSFET MAXIMUM RATINGS (T_A = 25°C unless otherwise noted)

Symbol	Parameter		Q1	Q2	Unit
V _{DS}	Drain to Source Voltage		30	30	V
V _{GS}	Gate to Source Voltage		±20	±20	V
I _D	Drain Current	– Continuous (Package limited) T _C = 25°C	20	55	A
		– Continuous T _A = 25°C	13 (Note 1a)	26 (Note 1b)	
		– Pulsed	40	100	
E _{AS}	Single Pulse Avalanche Energy (Note 3)		21	97	mJ
P _D	Power Dissipation for Single Operation	T _A = 25°C	1.6 (Note 1a)	2.0 (Note 1b)	W
		T _A = 25°C	0.8 (Note 1c)	0.9 (Note 1d)	
T _J , T _{STG}	Operating and Storage Junction Temperature Range		–55 to +150		°C

Stresses exceeding those listed in the Maximum Ratings table may damage the device. If any of these limits are exceeded, device functionality should not be assumed, damage may occur and reliability may be affected.

THERMAL CHARACTERISTICS

Symbol	Characteristic	Value	Value	Unit
R _{θJA}	Thermal Resistance, Junction to Ambient	77 (Note 1a)	63 (Note 1b)	°C/W
R _{θJA}	Thermal Resistance, Junction to Ambient	151 (Note 1c)	135 (Note 1d)	
R _{θJC}	Thermal Resistance, Junction to Case	5.0	3.5	

ELECTRICAL CHARACTERISTICS (T_J = 25°C unless otherwise noted)

Symbol	Parameter	Test Condition	Type	Min	Typ	Max	Unit
OFF CHARACTERISTICS							
BV _{DSS}	Drain to Source Breakdown Voltage	I _D = 250 μA, V _{GS} = 0 V I _D = 1 mA, V _{GS} = 0 V	Q1 Q2	30 30	– –	– –	V
$\frac{\Delta BV_{DSS}}{\Delta T_J}$	Breakdown Voltage Temperature Coefficient	I _D = 250 μA, referenced to 25°C I _D = 10 mA, referenced to 25°C	Q1 Q2	– –	16 20	– –	mV/°C
I _{DSS}	Zero Gate Voltage Drain Current	V _{DS} = 24 V, V _{GS} = 0 V V _{DS} = 24 V, V _{GS} = 0 V	Q1 Q2	– –	– –	1 500	μA μA
I _{GSS}	Gate to Source Leakage Current, Forward	V _{GS} = 20 V, V _{DS} = 0 V V _{GS} = 20 V, V _{DS} = 0 V	Q1 Q2	– –	– –	100 100	nA nA

ON CHARACTERISTICS

V _{GS(th)}	Gate to Source Threshold Voltage	V _{GS} = V _{DS} , I _D = 250 μA V _{GS} = V _{DS} , I _D = 1 mA	Q1 Q2	1.2 1.2	1.5 1.7	3.0 3.0	V
$\frac{\Delta V_{GS(th)}}{\Delta T_J}$	Gate to Source Threshold Voltage Temperature Coefficient	I _D = 250 μA, referenced to 25°C I _D = 10 mA, referenced to 25°C	Q1 Q2	– –	–5 –6	– –	mV/°C
R _{DS(on)}	Drain to Source On Resistance	V _{GS} = 10 V, I _D = 13 A V _{GS} = 4.5 V, I _D = 10 A V _{GS} = 10 V, I _D = 13 A, T _J = 125°C	Q1	– – –	4.6 6.7 6.6	6.4 9.6 9.2	mΩ
		V _{GS} = 10 V, I _D = 26 A V _{GS} = 4.5 V, I _D = 22 A V _{GS} = 10 V, I _D = 26 A, T _J = 125°C	Q2	– – –	1.4 2.0 1.9	1.9 2.7 2.6	
g _{FS}	Forward Transconductance	V _{DS} = 5 V, I _D = 13 A	Q1	–	53	–	S
		V _{DS} = 5 V, I _D = 26 A	Q2	–	168	–	

DYNAMIC CHARACTERISTICS

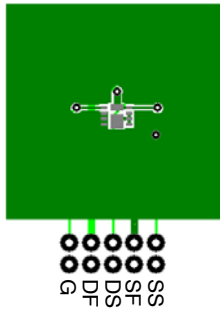
C _{iss}	Input Capacitance	Q1: V _{DS} = 15 V, V _{GS} = 0 V, f = 1 MHz Q2: V _{DS} = 15 V, V _{GS} = 0 V, f = 1 MHz	Q1 Q2	– –	827 2785	– –	pF
C _{oss}	Output Capacitance		Q1 Q2	– –	333 997	– –	pF
C _{rss}	Reverse Transfer Capacitance		Q1 Q2	– –	44 128	– –	pF
R _g	Gate Resistance		Q1	–	0.5	–	Ω
			Q2	–	0.5	–	

ELECTRICAL CHARACTERISTICS ($T_J = 25^\circ\text{C}$ unless otherwise noted) (continued)

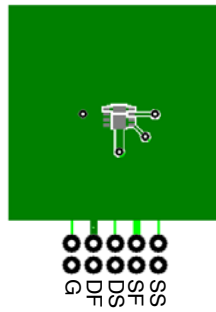
Symbol	Parameter	Test Condition		Type	Min	Typ	Max	Unit
SWITCHING CHARACTERISTICS								
t _{d(on)}	Turn-On Delay Time	Q1: V _{DD} = 15 V, I _D = 13 A, R _{GEN} = 6 Ω Q2: V _{DD} = 15 V, I _D = 26 A, R _{GEN} = 6 Ω		Q1	–	6	–	ns
t _r	Rise Time			Q2	–	11	–	ns
t _{d(off)}	Turn-Off Delay Time			Q1	–	2	–	ns
t _f	Fall Time			Q2	–	30	–	ns
Q _g	Total Gate Charge	V _{GS} = 0 V to 10 V	Q1 V _{DD} = 15 V, I _D = 13 A Q2 V _{DD} = 15 V, I _D = 26 A	Q1	–	13	–	nC
		V _{GS} = 0 V to 4.5 V		Q2	–	44	–	nC
Q _{gs}	Gate to Source Gate Charge			Q1	–	6	–	nC
Q _{gd}	Gate to Drain “Miller” Charge			Q2	–	21	–	nC
Q _{gs}	Gate to Source Gate Charge			Q1	–	2.2	–	nC
Q _{gd}	Gate to Drain “Miller” Charge			Q2	–	7.2	–	nC
Q _{gd}	Gate to Drain “Miller” Charge			Q1	–	1.9	–	nC
				Q2	–	6.6	–	nC
DRAIN-SOURCE DIODE CHARACTERISTICS								
V _{SD}	Source to Drain Diode Forward Voltage	V _{GS} = 0 V, I _S = 13 A (Note 2) V _{GS} = 0 V, I _S = 26 A (Note 2)		Q1	–	0.80	1.2	V
t _{rr}	Reverse Recovery Time	Q1: I _F = 13 A, di/dt = 100 A/μs Q2: I _F = 26 A, di/dt = 300 A/μs		Q1	–	0.77	1.2	ns
Q _{rr}	Reverse Recovery Charge			Q2	–	22	–	ns
				Q1	–	7	–	nC
				Q2	–	30	–	nC

Product parametric performance is indicated in the Electrical Characteristics for the listed test conditions, unless otherwise noted. Product performance may not be indicated by the Electrical Characteristics if operated under different conditions.

- $R_{\theta JA}$ is determined with the device mounted on a 1 in² pad 2 oz copper pad on a 1.5 × 1.5 in. board of FR-4 material. $R_{\theta JC}$ is guaranteed by design while $R_{\theta CA}$ is determined by the user's board design.



a. 77°C/W when mounted on a 1 in² pad of 2 oz copper



b. 63°C/W when mounted on a 1 in² pad of 2 oz copper



c. 151°C/W when mounted on a minimum pad of 2 oz copper



d. 135°C/W when mounted on a minimum pad of 2 oz copper

- Pulse Test: Pulse Width < 300 μs , Duty cycle < 2.0%.
- Q1: E_{AS} of 21 mJ is based on starting $T_J = 25^\circ\text{C}$; N-ch: $L = 1.2\text{ mH}$, $I_{AS} = 6\text{ A}$, $V_{DD} = 23\text{ V}$, $V_{GS} = 10\text{ V}$. 100% test at $L = 0.1\text{ mH}$, $I_{AS} = 14.5\text{ A}$.
Q2: E_{AS} of 97 mJ is based on starting $T_J = 25^\circ\text{C}$; N-ch: $L = 0.6\text{ mH}$, $I_{AS} = 18\text{ A}$, $V_{DD} = 23\text{ V}$, $V_{GS} = 10\text{ V}$. 100% test at $L = 0.1\text{ mH}$, $I_{AS} = 32.9\text{ A}$.
- As an N-ch device, the negative V_{GS} rating is for low duty cycle pulse occurrence only. No continuous rating is implied.

TYPICAL CHARACTERISTICS (Q1 N-CHANNEL) ($T_J = 25^\circ\text{C}$ unless otherwise noted)

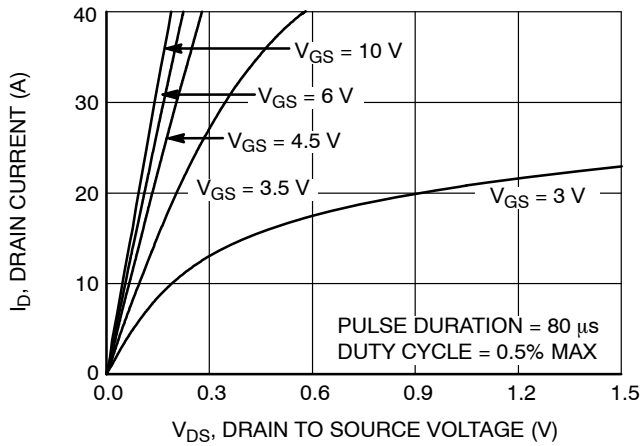


Figure 1. On-Region Characteristics

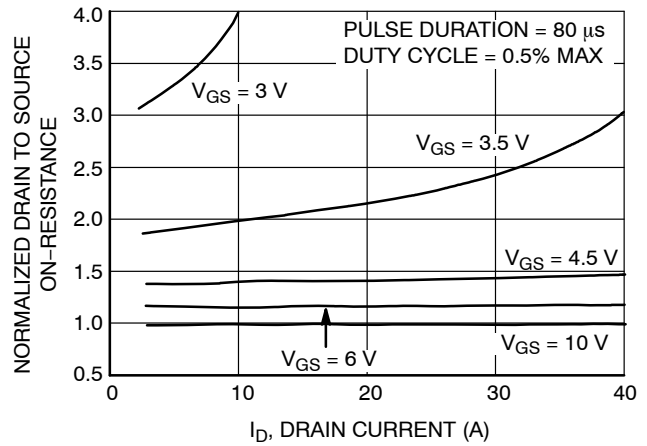


Figure 2. Normalized On-Resistance vs. Drain Current and Gate Voltage

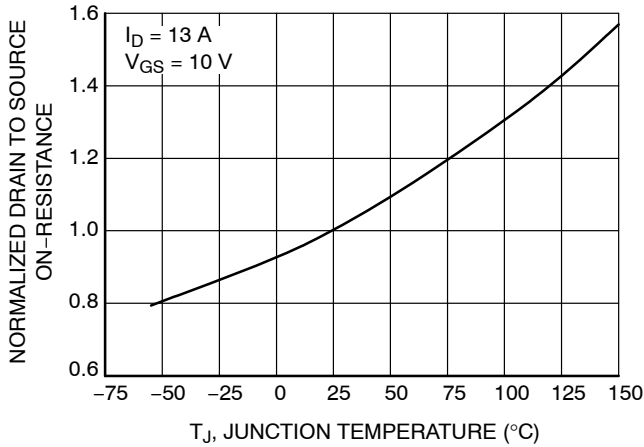


Figure 3. Normalized On-Resistance vs. Junction Temperature

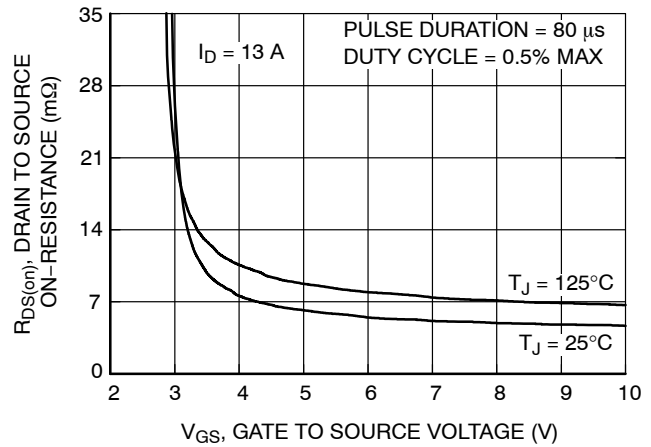


Figure 4. On-Resistance vs. Gate to Source Voltage

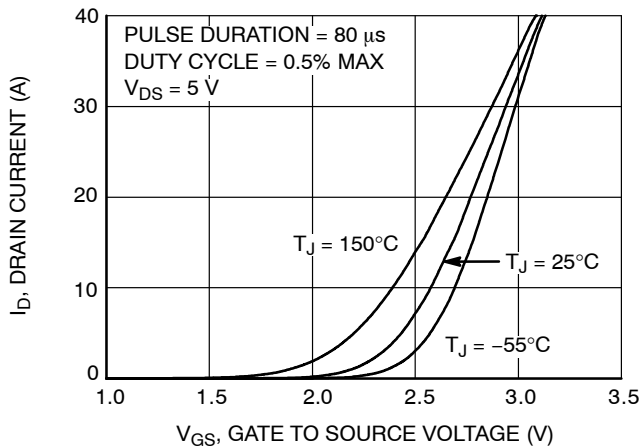


Figure 5. Transfer Characteristics

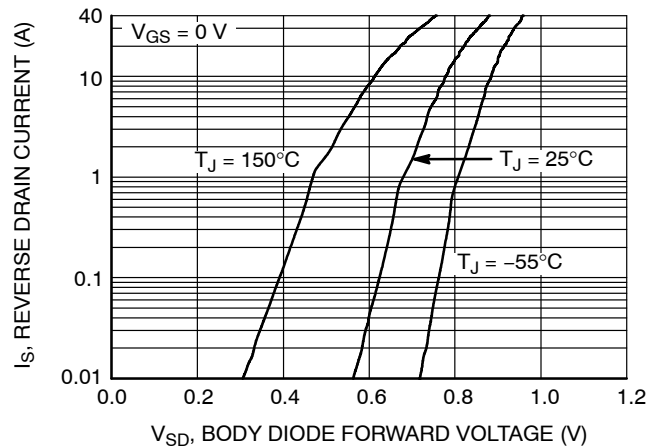


Figure 6. Source to Drain Diode Forward Voltage vs. Source Current

TYPICAL CHARACTERISTICS (Q1 N-CHANNEL) ($T_J = 25^\circ\text{C}$ unless otherwise noted) (continued)

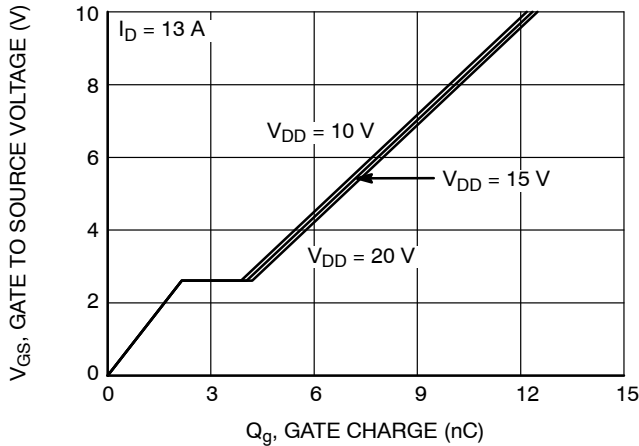


Figure 7. Gate Charge Characteristics

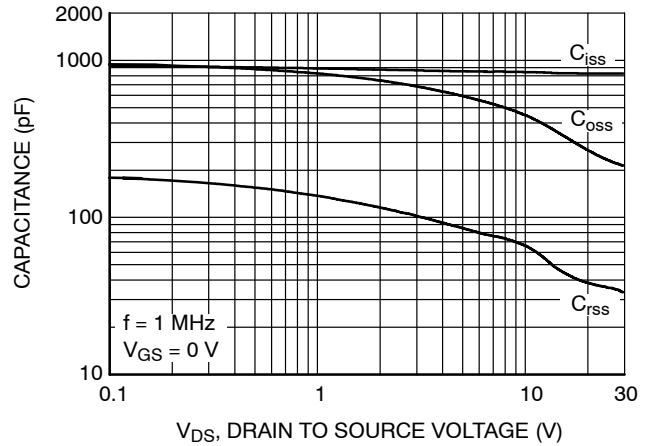


Figure 8. Capacitance vs. Drain to Source Voltage

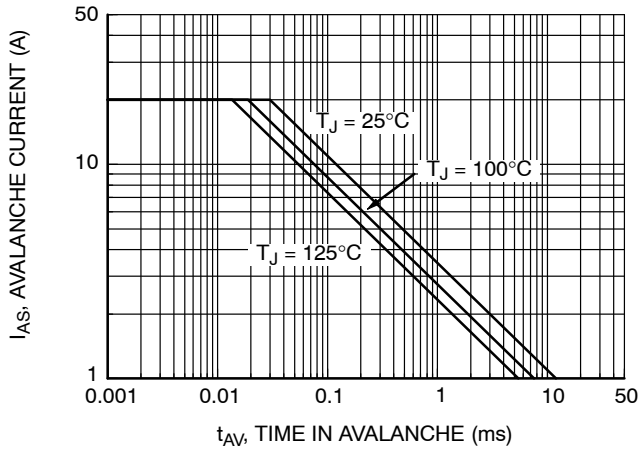


Figure 9. Unclamped Inductive Switching Capability

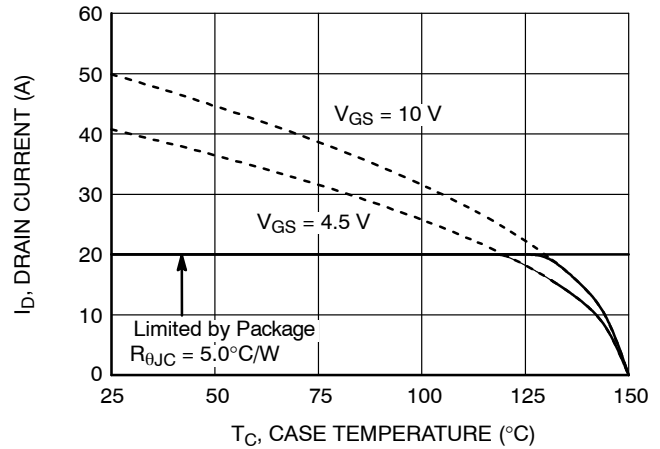


Figure 10. Maximum Continuous Drain Current vs. Case Temperature

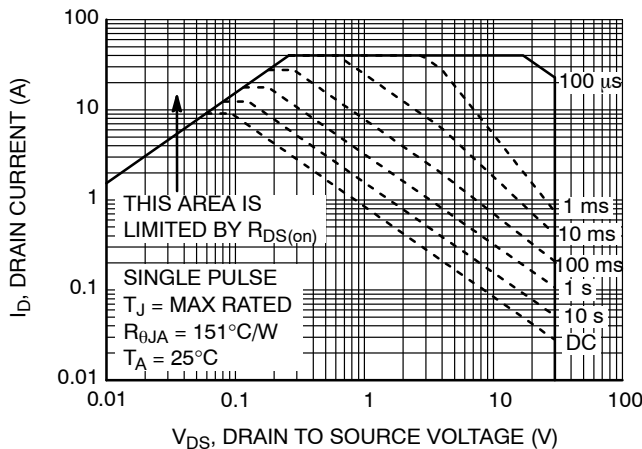


Figure 11. Forward Bias Safe Operating Area

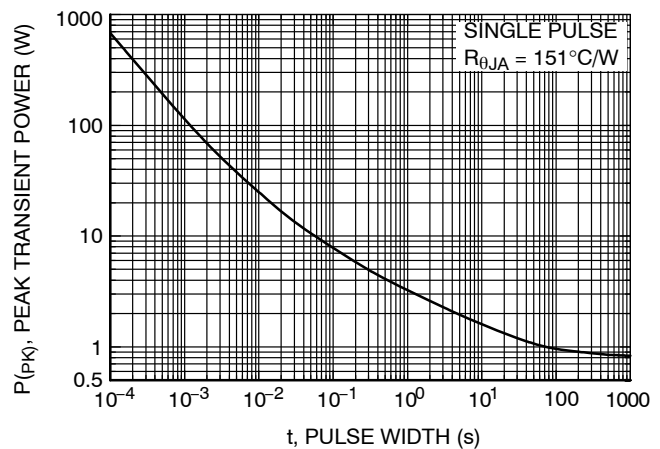


Figure 12. Single Pulse Maximum Power Dissipation

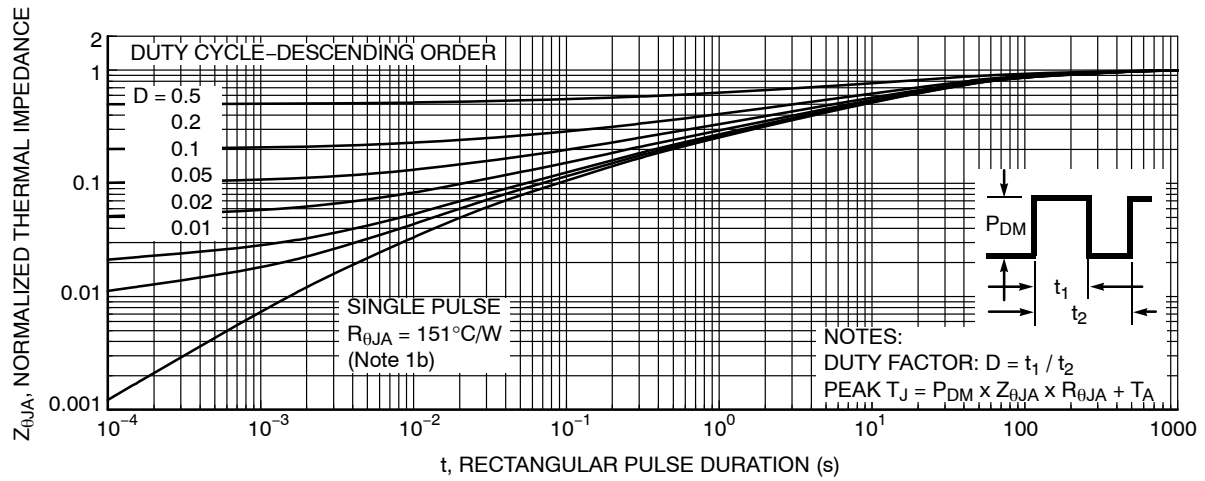
TYPICAL CHARACTERISTICS (Q1 N-CHANNEL) ($T_J = 25^\circ\text{C}$ unless otherwise noted) (continued)

Figure 13. Junction-to-Ambient Transient Thermal Response Curve

TYPICAL CHARACTERISTICS (Q2 N-CHANNEL) ($T_J = 25^\circ\text{C}$ unless otherwise noted)

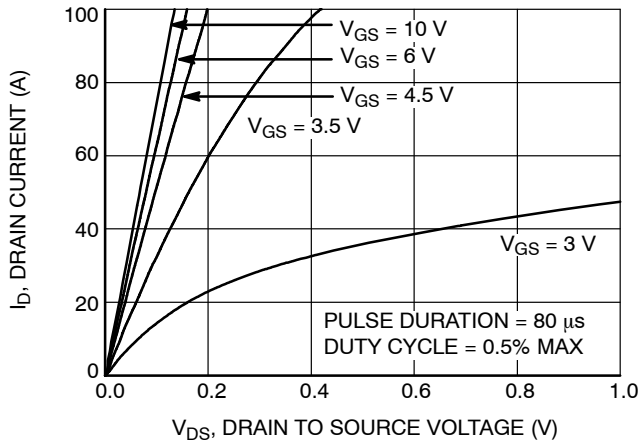


Figure 14. On-Region Characteristics

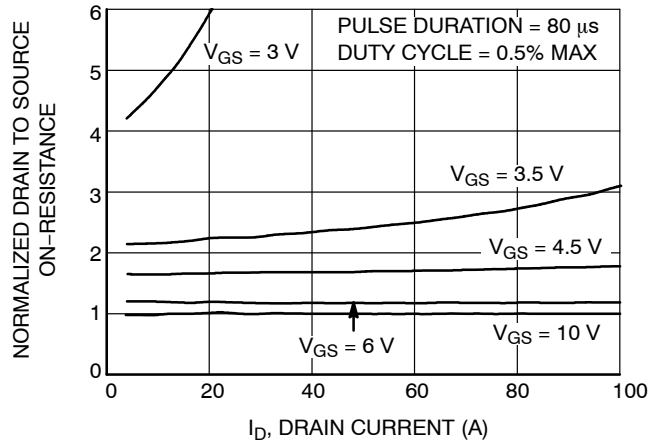


Figure 15. Normalized On-Resistance vs. Drain Current and Gate Voltage

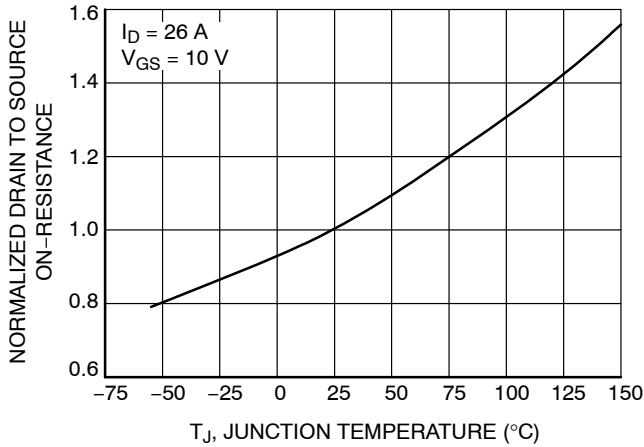


Figure 16. Normalized On-Resistance vs. Junction Temperature

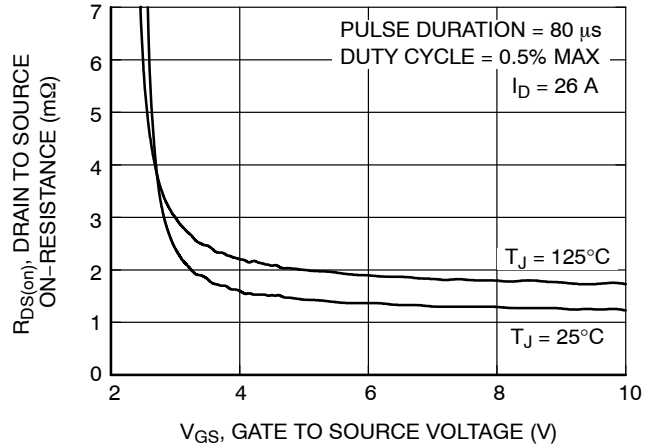


Figure 17. On-Resistance vs. Gate to Source Voltage

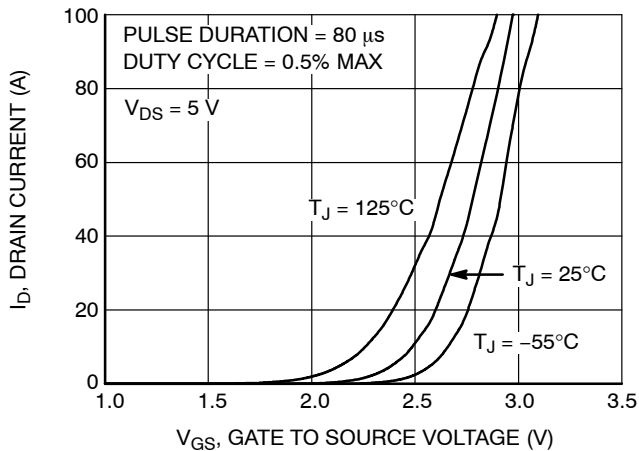


Figure 18. Transfer Characteristics

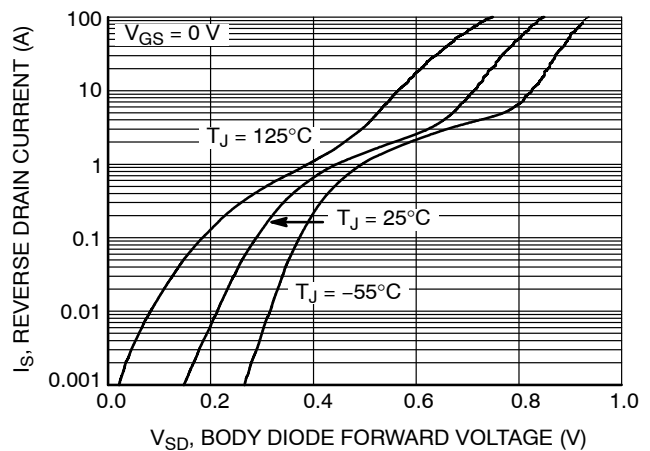


Figure 19. Source to Drain Diode Forward Voltage vs. Source Current

TYPICAL CHARACTERISTICS (Q2 N-CHANNEL) ($T_J = 25^\circ\text{C}$ unless otherwise noted) (continued)

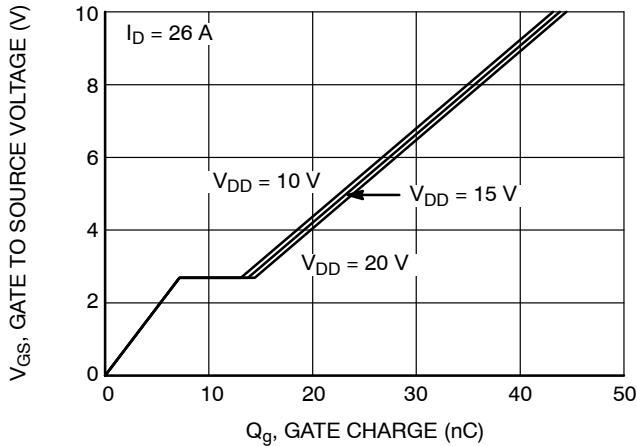


Figure 20. Gate Charge Characteristics

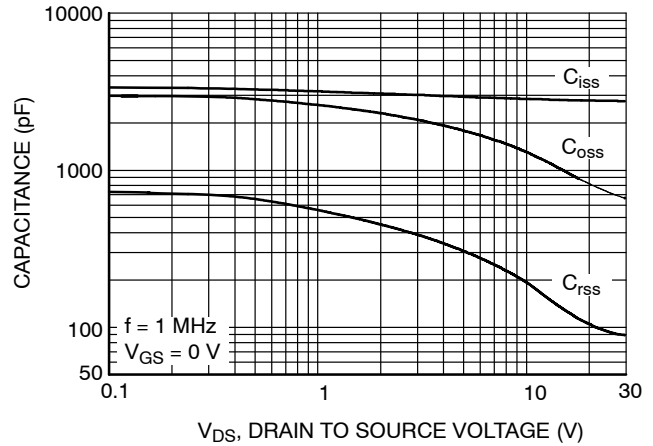


Figure 21. Capacitance vs. Drain to Source Voltage

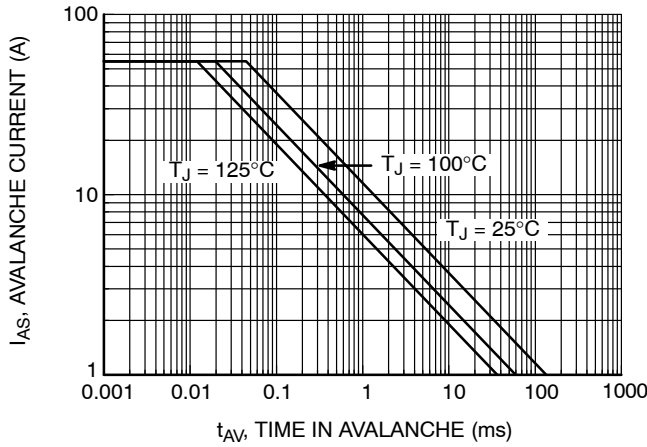


Figure 22. Unclamped Inductive Switching Capability

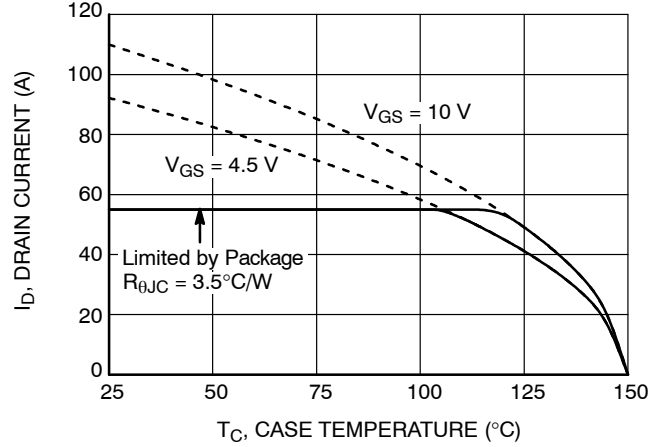


Figure 23. Maximum Continuous Drain Current vs. Ambient Temperature

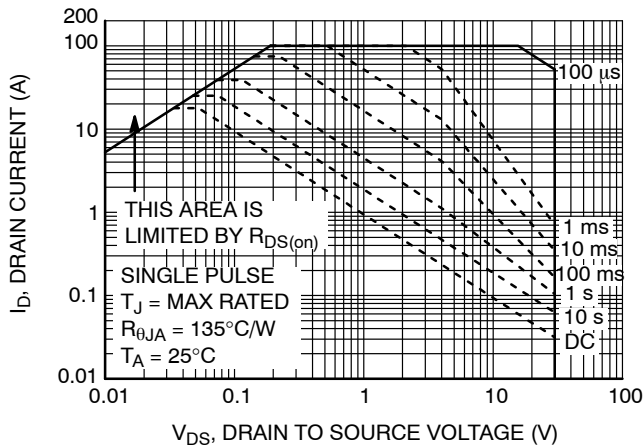


Figure 24. Forward Bias Safe Operating Area

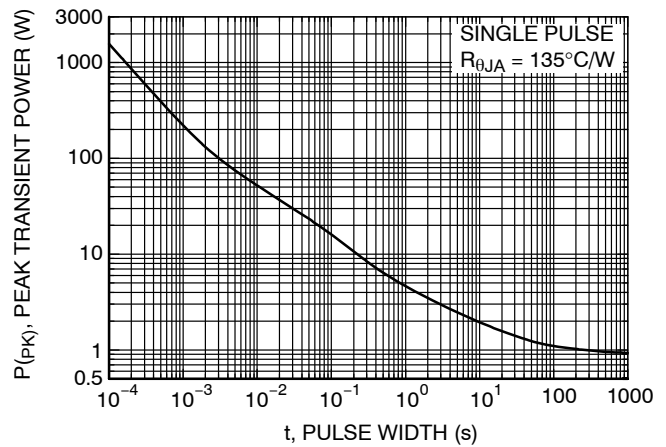
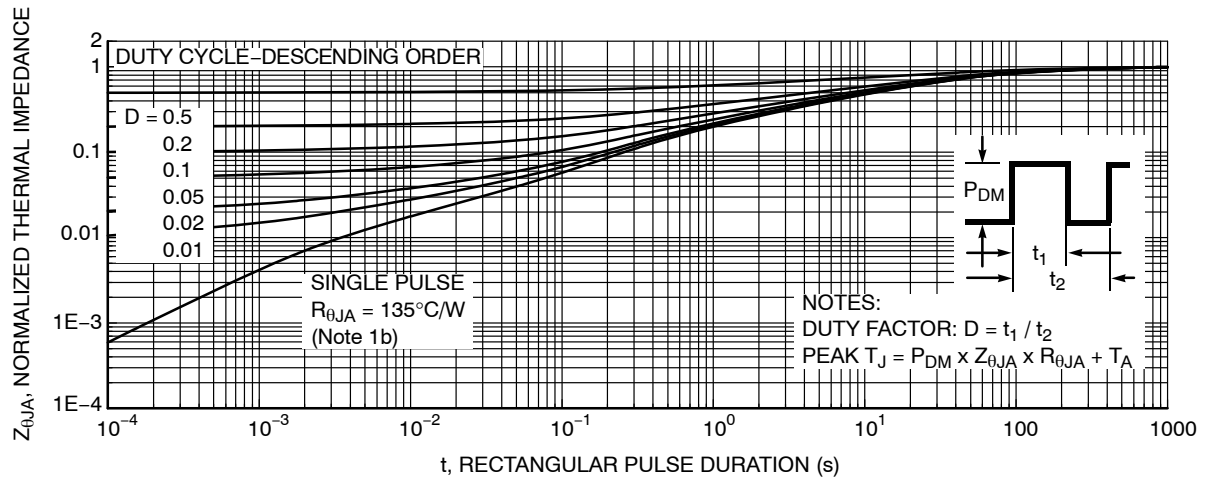


Figure 25. Single Pulse Maximum Power Dissipation

TYPICAL CHARACTERISTICS (Q2 N-CHANNEL) ($T_J = 25^\circ\text{C}$ unless otherwise noted) (continued)

TYPICAL CHARACTERISTICS (continued)

SyncFET Schottky Body Diode Characteristics

onsemi's SyncFET process embeds a Schottky diode in parallel with POWERTRENCH MOSFET. This diode exhibits similar characteristics to a discrete external Schottky diode in parallel with a MOSFET. Figure 27 shows the reverse recovery characteristic of the FDPC8013S.

Schottky barrier diodes exhibit significant leakage at high temperature and high reverse voltage. This will increase the power in the device.

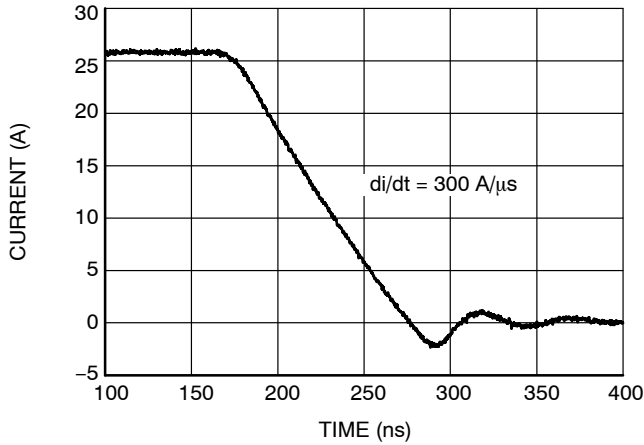


Figure 27. FDPC8013S SyncFET Body Diode Reverse Recovery Characteristics

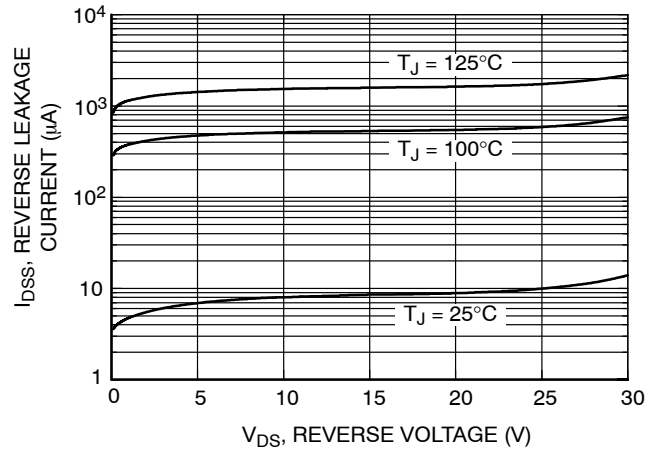
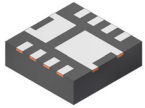


Figure 28. SyncFET Body Diode Reverse Leakage vs. Drain-Source Voltage

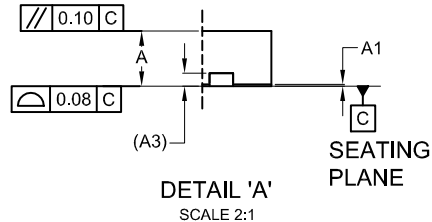
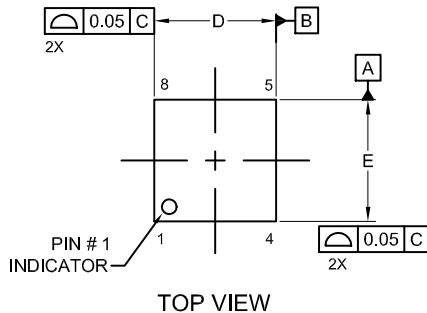
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SyncFET is a trademark of Semiconductor Components Industries, LLC dba "onsemi" or its affiliates and/or subsidiaries in the United States and/or other countries.



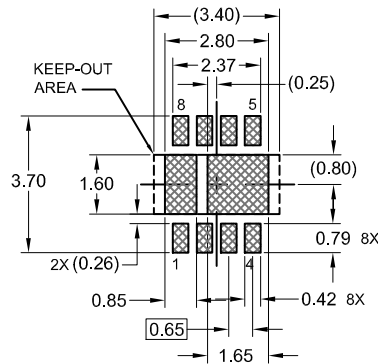
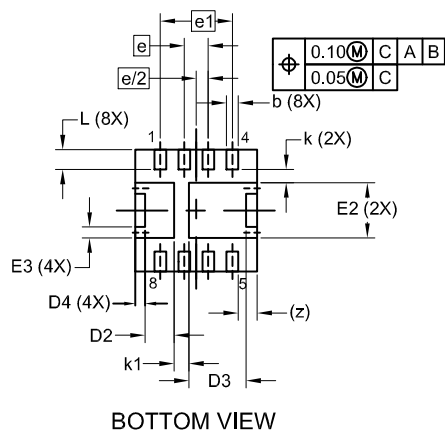
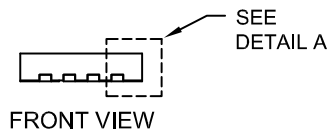
PQFN8 3.3X3.3, 0.65P
CASE 483AZ
ISSUE B

DATE 14 FEB 2022



NOTES:

1. DIMENSIONING AND TOLERANCING PER ASME Y14.5M, 2009.
2. CONTROLLING DIMENSION: MILLIMETERS
3. COPLANARITY APPLIES TO THE EXPOSED PADS AS WELL AS THE TERMINALS.
4. DIMENSIONS DO NOT INCLUDE BURRS OR MOLD FLASH. MOLD FLASH OR BURRS DOES NOT EXCEED 0.10MM.
5. SEATING PLANE IS DEFINED BY THE TERMINALS. "A1" IS DEFINED AS THE DISTANCE FROM THE SEATING PLANE TO THE LOWEST POINT ON THE PACKAGE BODY.
6. IT IS RECOMMENDED TO HAVE NO TRACES OR VIAS WITHIN THE KEEP OUT AREA.



*FOR ADDITIONAL INFORMATION ON OUR PB-FREE STRATEGY AND SOLDERING DETAILS, PLEASE DOWNLOAD THE ON SEMICONDUCTOR SOLDERING AND MOUNTING TECHNIQUES REFERENCE MANUAL, SOLDERM/D.

DIM	MILLIMETERS		
	MIN	NOM	MAX
A	0.70	0.75	0.80
A1	0.00	--	0.05
A3	0.20 REF		
b	0.27	0.32	0.37
D	3.20	3.30	3.40
D2	0.69	0.79	0.89
D3	1.45	1.55	1.65
D4	0.16	0.26	0.36
E	3.20	3.30	3.40
E2	1.40	1.50	1.60
E3	0.30 REF		
e	0.65 BSC		
e1	1.95 BSC		
e/2	0.325 BSC		
k	0.36 REF		
k1	0.40 REF		
L	0.44	0.54	0.64
z	0.52 REF		

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DESCRIPTION: PQFN8 3.3X3.3, 0.65P

PAGE 1 OF 1

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